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Gallium Nitride Materials and Devices XI

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15–18 February 2016
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 9748

Proceedings of SPIE 0277-786X, V. 9748

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Gallium Nitride Materials and Devices XI, edited by Jen-Inn Chyi, Hiroshi Fujioka, Hadis Morkoç,
Yasushi Nanishi, Ulrich T. Schwarz, Jong-In Shim, Proc. of SPIE Vol. 9748, 974801
© 2016 SPIE · CCC code: 0277-786X/16/$18 · doi: 10.1117/12.2239452

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Author(s), "Title of Paper," in *Gallium Nitride Materials and Devices XI*, edited by Jen-Inn Chyi, Hiroshi Fujioka, Hadis Morkoç, Yasushi Nanishi, Ulrich T. Schwarz, Jong-In Shim, Proceedings of SPIE Vol. 9748 (SPIE, Bellingham, WA, 2016) Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)
ISBN: 9781628419832

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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